25. (Amended) The method for manufacturing a three-dimensional device according to claim 21, the at least one thin film device layer being deposited by transferring being formed simultaneously with at least one other of the thin film device layers.

Please add new claims 26 and 27 as follows:

--26. (New) The method for manufacturing a three-dimensional device according to claim 21, at least one of the plurality of thin film device layers having a light-emitting section.--

--27. (New) The method for manufacturing a three-dimensional device according to claim 21, further comprising a step of forming a light-emitting section in at least one of the plurality of thin film device layers.--

REMARKS

Claims 1-27 are pending. By this Amendment, claims 1-25 are amended, and claims 26 and 27 are added.

Applicants appreciate the courtesies extended to Applicants' representative by Examiner Flynn and Examiner Fordé during the December 19 interview.

The attached Appendix includes marked-up copies of each rewritten claim (37 C.F.R. §1.121(c)(1)(ii)).

I. The Claims Define Patentable Subject Matter

The June 29 Office Action rejects claims 1-9 and 12-14 under 35 U.S.C. §102(a) over Zavracky et al. (U.S. Patent No. 5,656,548); and claim 10 under 35 U.S.C. §103(a) over Zavracky et al. in view of Yoshizawa et al. (U.S. Patent No. 5,819,406). These rejections are respectfully traversed.

During the December 19 interview, Examiner Flynn and Examiner Fordé indicated that claims 21-25 are allowable over the applied references. For similar reasons, claims 1-20 which are rewritten as method claims, should also be indicated as being allowable.

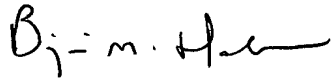
For at least these reasons, it is respectfully submitted that claims 1-27 are patentable over the applied references. Applicants respectfully request that the rejections under 35 U.S.C. §102 and §103 be withdrawn.

II. Conclusion

In view of the foregoing, Applicants respectfully submit that this application is in condition for allowance. Favorable consideration and prompt allowance are earnestly solicited.

Should the Examiner believe anything further is desirable in order to place this application in even better condition for allowance, the Examiner is invited to contact Applicants' undersigned representative at the telephone number listed below.

Respectfully submitted,



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Attachments:
Appendix
Amendment Transmittal

Date: January 9, 2002

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DEPOSIT ACCOUNT USE AUTHORIZATION
Please grant any extension necessary for entry;
Charge any fee due to our Deposit Account No. 15-0461

APPENDIX

Changes to Claims:

Claims 26 and 27 are added.

The following is a marked-up version of the amended claim:

1. (Three Times Amended) A method of forming ~~A~~a three-dimensional device ~~comprising:~~having

~~———~~a plurality of thin film device layers deposited in a thickness direction, and a first substrate, each thin film device layer being disposed in a predetermined region in a planar direction, comprising:

depositing at least one of the thin film device layers ~~being deposited~~ by ~~a transfer method including~~ a separation in a separable layer on which the at least one thin film device layer is formed.

2. (Three Times Amended) The method of forming ~~A~~a three-dimensional device ~~comprising:~~having

~~————~~a plurality of thin film device layers deposited on a base in a thickness direction for constituting a three-dimensional circuit, each thin film device layer constituting a circuit disposed in a predetermined region extending in a planar direction, comprising:

depositing at least one of the thin film device layers ~~being deposited~~ by ~~a transfer method including~~ a separation in a separable layer on which the at least one thin film device layer is formed.

3. (Three Times Amended) The method of forming a three-dimensional device according to claim 1, further ~~comprising a first substrate, the transfer method~~ comprising forming the at least one thin film device layer on a second substrate with the separable layer therebetween~~,~~; and

~~———~~irradiating the separable layer with light to cause a separation in at least one

of the separable layer and at an interface so that the at least one thin film device layer on the second substrate is transferred to the first substrate of the three-dimensional device.

4. (Twice Amended) The method of forming a three-dimensional device according to claim 3, the separation of the separable layer being caused by one of breakage and weakening of interatomic or intermolecular bonds in a material constituting the separable layer.

5. (Twice Amended) The method of forming a three-dimensional device according to claim 3, the separation of the separable layer ~~is~~ being caused by evolution of gas from a material constituting the separable layer.

6. (Twice Amended) The method of forming a three-dimensional device according to claim 3, the light being a laser beam.

7. (Twice Amended) The method of forming a three-dimensional device according to claim 3, the separable layer comprising one of amorphous silicon, ceramic, metal, and organic polymeric material.

8. (Twice Amended) The method of forming a three-dimensional device according to claim 1, each thin film device layer comprising electrodes electrically connecting two adjacent thin film device layers to each other.

9. (Twice Amended) The method of forming a three-dimensional device according to claim 8, the connecting electrodes being provided on both surfaces of each thin film device layer.

10. (Twice Amended) The method of forming a three-dimensional device according to claim 8, the three dimensional device further comprising an anisotropic conductive film, the method further comprising joining two adjacent thin film device layers ~~being joined~~ to each other with the anisotropic conductive film therebetween.

11. (Twice Amended) The method of forming a three-dimensional device

according to claim 1, in two selected layers of the thin film device layers, a first layer ~~having~~ has a light-emitting section and a second layer has a light-receiving section, the light-emitting section and the light-receiving section enabling optical communication between the two layers.

12. (Twice Amended) The method of forming a three-dimensional device according to claim 1, the at least one thin film device layer deposited by transferring being formed simultaneously with at least one other of the thin film device layers.

13. (Twice Amended) The method of forming a three-dimensional device according to claim 1, at least one of the thin film device layers comprising a plurality of thin film transistors.

14. (Twice Amended) The method of forming a three-dimensional device according to claim 1, at least one of the thin film device layers comprising a memory cell array.

15. (Twice Amended) The method of forming a three-dimensional device according to claim 1, a plurality of layers among the thin film device layers comprising one memory.

16. (Twice Amended) The method of forming a three-dimensional device according to claim 1, at least one of the thin film device layers comprising a memory cell array, and at least one other thin film device layers comprises a logic circuit.

17. (Twice Amended) The method of forming a three-dimensional device according to claim 16, the logic circuit driving the memory cell array.

18. (Twice Amended) The method of forming a three-dimensional device according to claim 16, the logic circuit and the memory cell array being formed in accordance with different design rules.

19. (Twice Amended) The method of forming a three-dimensional device

according to claim 16, the logic circuit and the memory cell array being formed in accordance with different design parameters.

20. (Twice Amended) The method of forming a three-dimensional device according to claim 16, the logic circuit and the memory cell array being formed by different fabricating processes.

21. (Amended) A method ~~of transferring~~for manufacturing a three-dimensional device having a plurality of thin film device layers ~~to~~ on a first substrate, comprising:

forming at least one thin film device layer on a second substrate with a separable layer therebetween; and

irradiating the separable layer with light to cause a separation in at least one of the separable layers and at an interface so that the at least one thin film device layer ~~on the second substrate~~ is transferred to the first substrate.

22. (Amended) The method ~~of transferring~~ for manufacturing a three-dimensional device according to claim 21, the separation of the separable layer being caused by one of breakage and weakening of interatomic or intermolecular bonds in a material constituting the separable layer.

23. (Amended) The method ~~of transferring~~for manufacturing a three-dimensional device according to claim 21, the separation of the separable layer being caused by evolution of gas from a material constituting the separable layer.

24. (Amended) The method ~~of transferring~~for manufacturing a three-dimensional device according to claim 21, the light being a laser beam.

25. (Amended) The method ~~of transferring~~for manufacturing a three-dimensional device according to claim 21, the at least one thin film device layer being deposited by transferring being formed simultaneously with at least one other of the thin film device layers.